

isc Silicon NPN Power Transistor

BUV48CFI

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)}= 700V (Min)
- · High Current Capability
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS



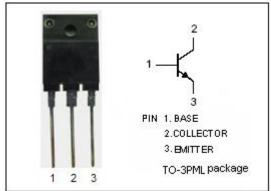
 Designed for switching and industrial applications from single and three-phase mains.

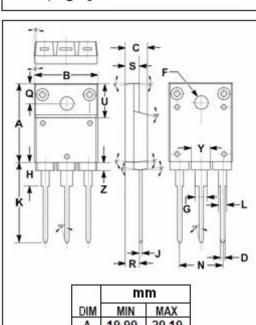
Absolute maximum ratings(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------------|
| V _{CBO} | Collector-Base Voltage | 1200 | V |
| V _{CEO} | Collector-Emitter Voltage | 700 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| Ic | Collector Current-Continuous | 15 | Α |
| I _{CM} | Collector Current-Peak tp< 5ms | 30 | Α |
| I _B | Base Current-Continuous | 4 | Α |
| I _{BM} | Base Current-peak t _p < 5ms | 20 | Α |
| Pc | Collector Power Dissipation @T _C =25°C | 65 | W |
| T _j | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------|-------------------------------------|-----|------|
| Rth j-c | Thermal Resistance,Junction to Case | 1.0 | °C/W |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 19.90 | 20.10 | |
| В | 15.75 | 16.10 | |
| C | 5.50 | 5.70 | |
| D | 0.90 | 1.10 | |
| F | 3.30 | 3.50 | |
| G | 2.90 | 3.20 | |
| Η | 5.90 | 6.10 | |
| J | 0.595 | 0.70 | |
| K | 21.10 | 22.50 | |
| L | 1.90 | 2.25 | |
| N | 10.80 | 11.00 | |
| Q | 4.90 | 5.10 | |
| R | 3.75 | 3.95 | |
| S | 3.20 | 3.60 | |
| U | 9.90 | 10.10 | |
| Y | 4.20 | 4.90 | |
| Z | 1.90 | 2.10 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|-------------------------|--|--|-----|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 50mA; I _B = 0 | 700 | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C = 6A; I _B = 1.5A | | 1.5 | V |
| V _{CE} (sat)-2 | Collector-Emitter Saturation Voltage I _C = 10A; I _B = 4A | | | 3.0 | V |
| V _{BE(sat)-1} | Base-Emitter Saturation Voltage | I _C = 6A; I _B = 1.5A | | 1.5 | V |
| V _{BE(sat)-2} | Base-Emitter Saturation Voltage | I _C = 10A; I _B = 4A | | 2.0 | V |
| Ісво | Collector Cutoff Current | V _{CB} = 1200V ; I _B = 0 | | 0.5 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 700V; I _B = 0 | | 1.0 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 6V; I _C = 0 | | 1.0 | mA |

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